

**COMPLEMENTARY NPN/PNP SURFACE MOUNT TRANSISTOR**

**Features**

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Ultra Small Package**

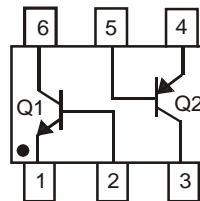
**Mechanical Data**

- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)

SOT-963



Top View



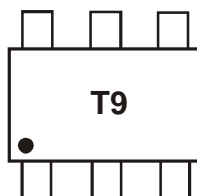
Device Schematic

**Ordering Information** (Note 5)

Device	Packaging	Shipping
DST3946DPJ-7	SOT-963	10,000/Tape & Reel

- Notes:
1. No purposefully added lead. Halogen and Antimony Free.
  2. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>

**Marking Information**



T9 = Product Type Marking Code

**Maximum Ratings - NPN (Q1)** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current – Continuous	I <sub>C</sub>	200	mA

**Maximum Ratings - PNP (Q2)** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous	I <sub>C</sub>	-200	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	R <sub>θJA</sub>	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 3. Device mounted on FR-4 PCB with minimum recommended pad layout.

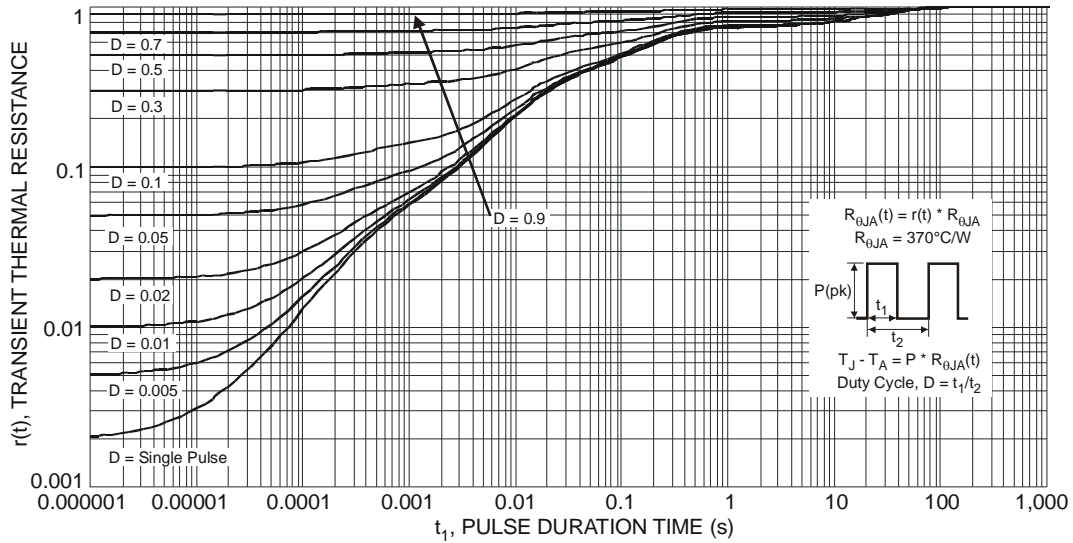


Fig. 1 Transient Thermal Response

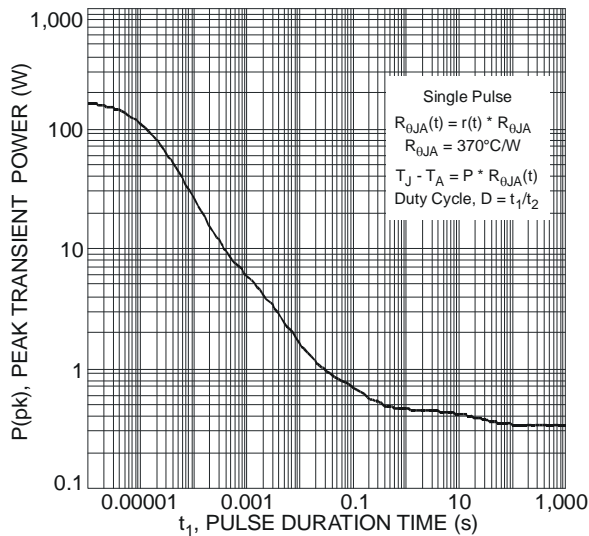


Fig. 2 Single Pulse Maximum Power Dissipation

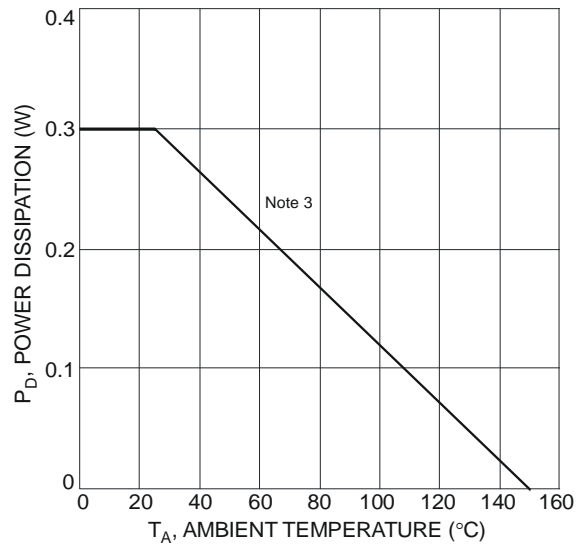


Fig. 3 Power Dissipation vs. Ambient Temperature

**Electrical Characteristics - NPN (Q1)** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition	
<b>OFF CHARACTERISTICS (Note 4)</b>						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	$I_C = 10\mu\text{A}, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 4)	$V_{(BR)CEO}$	40	—	V	$I_C = 1.0\text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$	
Collector Cutoff Current	$I_{CEX}$	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$	
Base Cutoff Current	$I_{BL}$	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$	
<b>ON CHARACTERISTICS (Note 4)</b>						
DC Current Gain	$h_{FE}$	40	—	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$	
		70	—			$I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$
		100	300			$I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$
		60	—			$I_C = 50\text{mA}, V_{CE} = 1.0\text{V}$
		30	—			$I_C = 100\text{mA}, V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.65 —	0.85 0.95	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$	
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	$C_{obo}$	—	4.0	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$	
Input Capacitance	$C_{ibo}$	—	8.5	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$	
Input Impedance	$h_{ie}$	1.0	10	k $\Omega$	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA},$ $f = 1.0\text{kHz}$	
Voltage Feedback Ratio	$h_{re}$	0.5	8.0	$\times 10^{-4}$		
Small Signal Current Gain	$h_{fe}$	100	400	—		
Output Admittance	$h_{oe}$	1.0	40	$\mu\text{S}$		
Current Gain-Bandwidth Product	$f_T$	300	—	MHz		$V_{CE} = 20\text{V}, I_C = 10\text{mA},$ $f = 100\text{MHz}$
<b>SWITCHING CHARACTERISTICS</b>						
Delay Time	$t_d$	—	35	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA},$ $V_{BE(off)} = -0.5\text{V}, I_{B1} = 1.0\text{mA}$	
Rise Time	$t_r$	—	35	ns		
Storage Time	$t_s$	—	200	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA},$ $I_{B1} = I_{B2} = 1.0\text{mA}$	
Fall Time	$t_f$	—	50	ns		

Notes: 4. Short duration pulse test used to minimize self-heating effect.

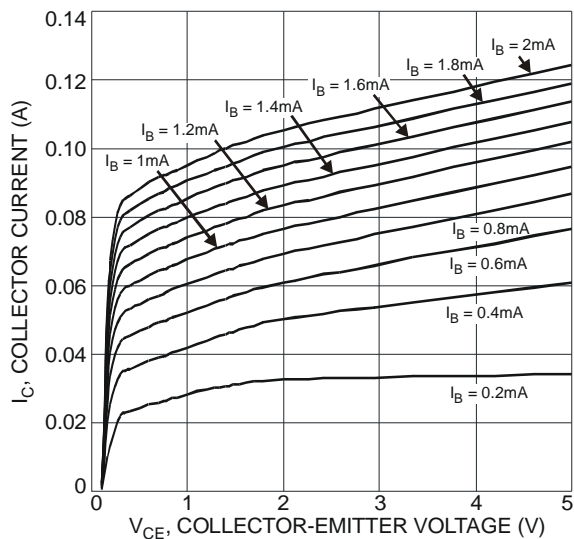


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

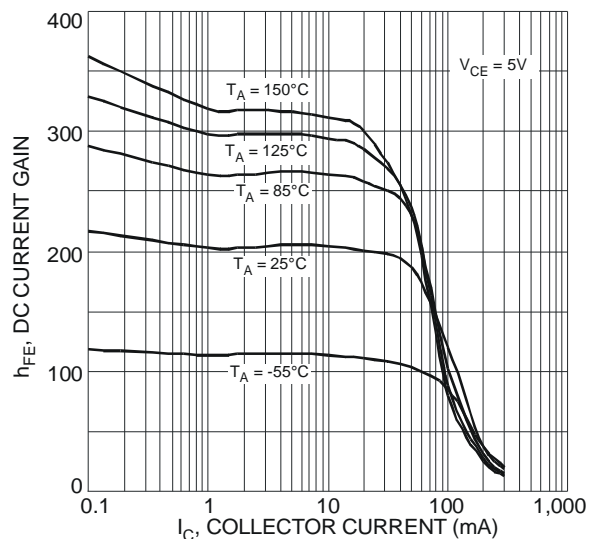


Fig. 5 Typical DC Current Gain vs. Collector Current

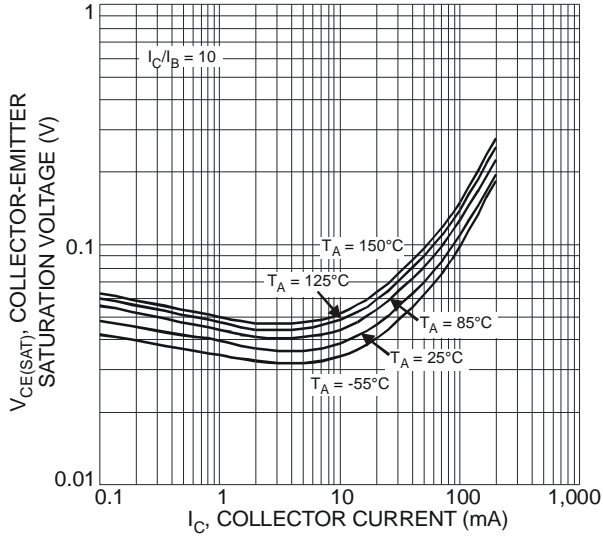


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

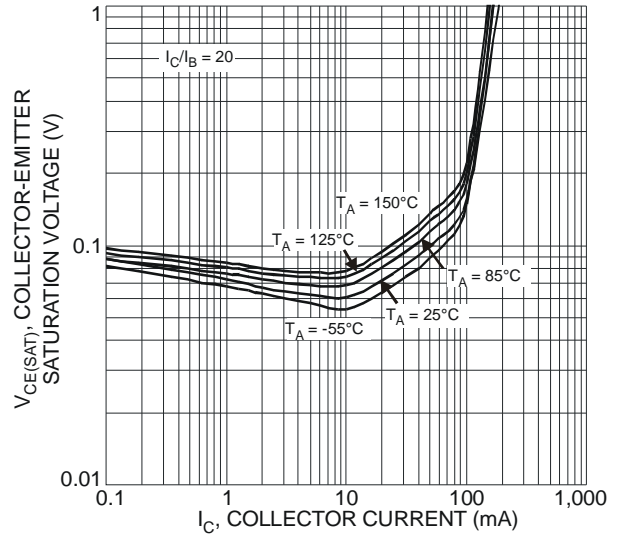


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

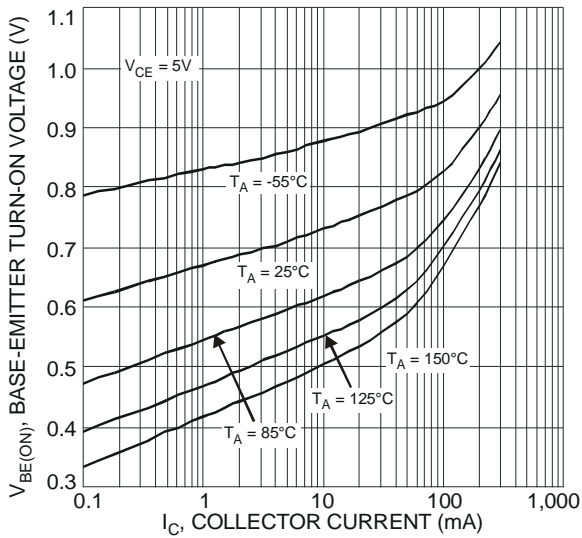


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

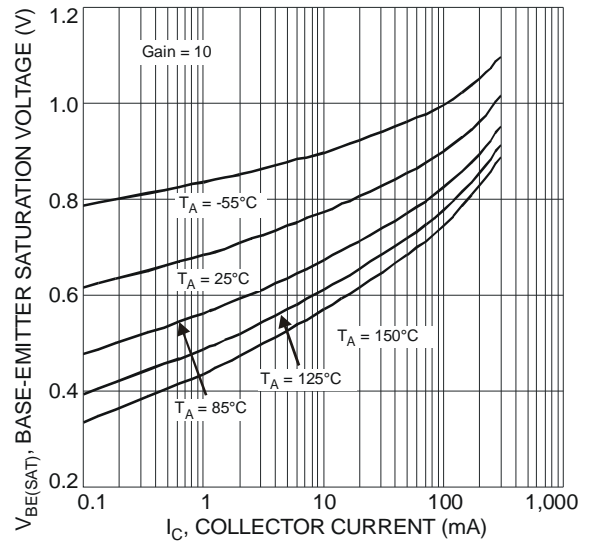


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

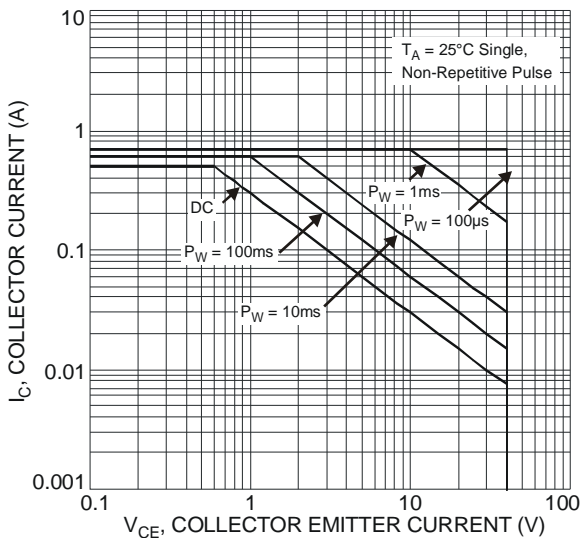


Fig. 10 Safe Operation Area (NPN)

**Electrical Characteristics - PNP (Q2)** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 4)	$V_{(BR)CEO}$	-40	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CEX}$	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$
	$I_{CBO}$	—	-50	nA	$V_{CE} = -30\text{V}, I_E = 0$
Base Cutoff Current	$I_{BL}$	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$
<b>ON CHARACTERISTICS (Note 4)</b>					
DC Current Gain	$h_{FE}$	60	—	—	$I_C = -100\mu\text{A}, V_{CE} = -1.0\text{V}$
		80	—		$I_C = -1.0\text{mA}, V_{CE} = -1.0\text{V}$
		100	300		$I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$
		60	—		$I_C = -50\text{mA}, V_{CE} = -1.0\text{V}$
		30	—		$I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	4.5	pF	$V_{CB} = -5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	$C_{ibo}$	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	$h_{ie}$	2.0	12	$k\Omega$	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA},$ $f = 1.0\text{kHz}$
Voltage Feedback Ratio	$h_{re}$	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	$h_{fe}$	100	400	—	
Output Admittance	$h_{oe}$	3.0	60	$\mu\text{S}$	
Current Gain-Bandwidth Product	$f_T$	300	—	MHz	
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	$t_d$	—	35	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA},$ $V_{BE(off)} = 0.5\text{V}, I_{B1} = -1.0\text{mA}$
Rise Time	$t_r$	—	35	ns	
Storage Time	$t_s$	—	225	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA},$ $I_{B1} = I_{B2} = -1.0\text{mA}$
Fall Time	$t_f$	—	75	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

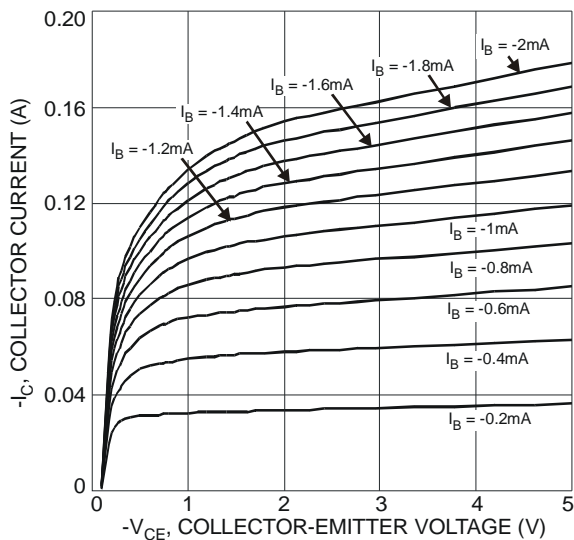


Fig. 11 Typical Collector Current vs. Collector-Emitter Voltage

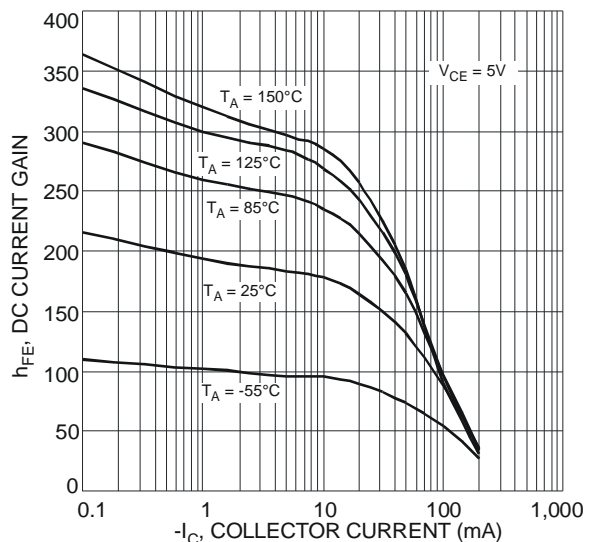


Fig. 12 Typical DC Current Gain vs. Collector Current

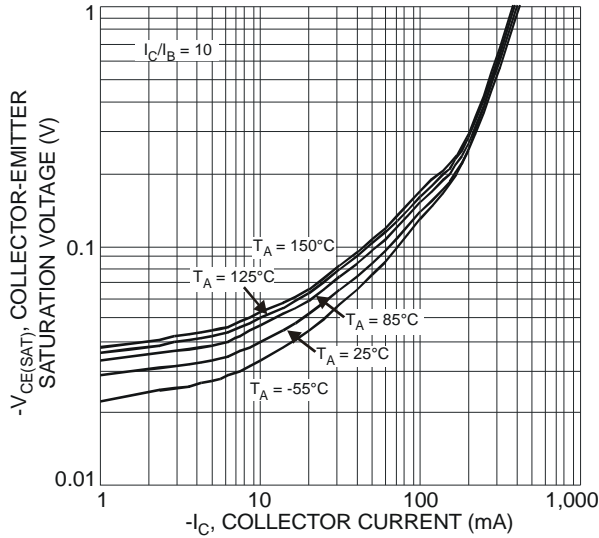


Fig. 13 Typical Collector-Emitter Saturation Voltage vs. Collector Current

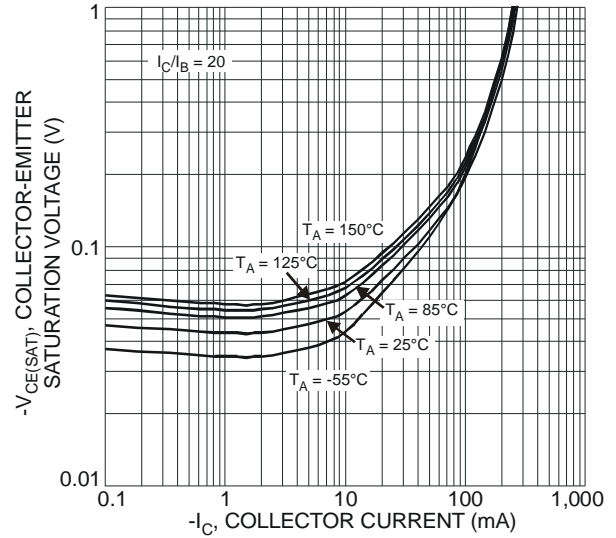


Fig. 14 Typical Collector-Emitter Saturation Voltage vs. Collector Current

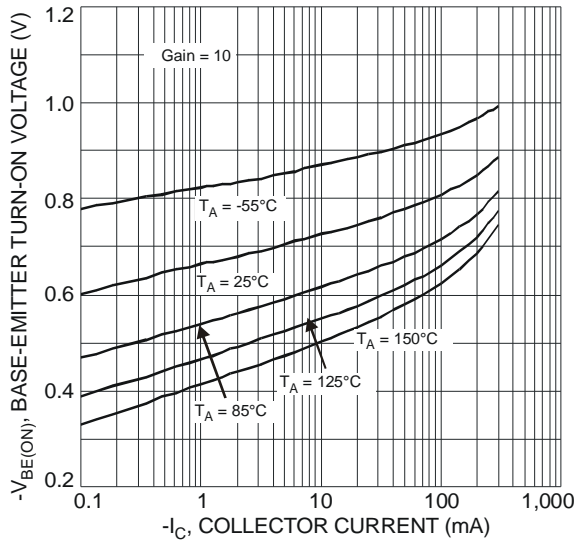


Fig. 15 Typical Base-Emitter Saturation Voltage vs. Collector Current

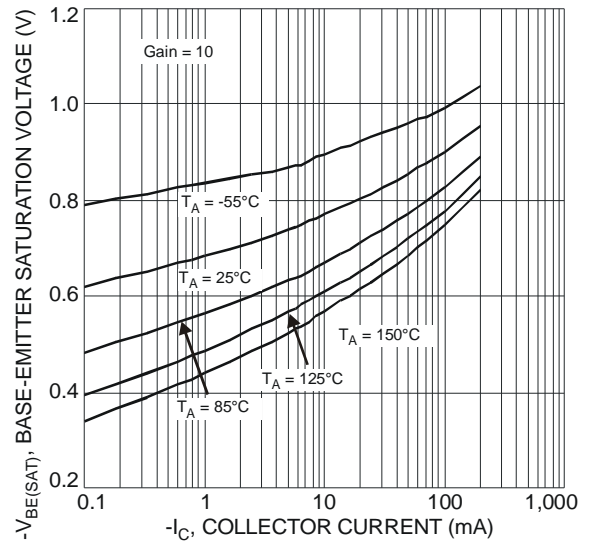


Fig. 16 Typical Base-Emitter Saturation Voltage vs. Collector Current

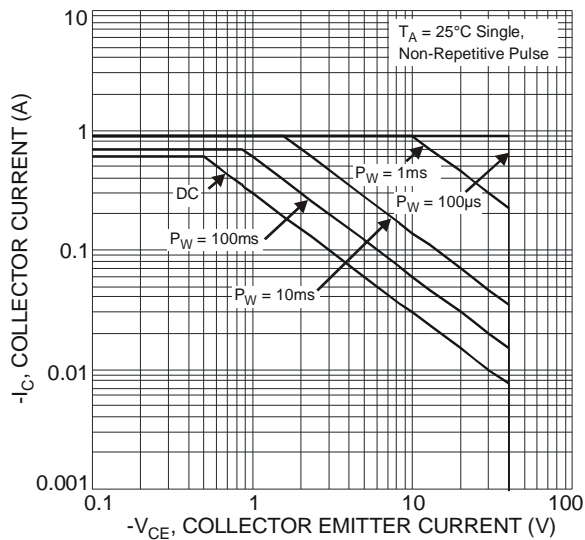
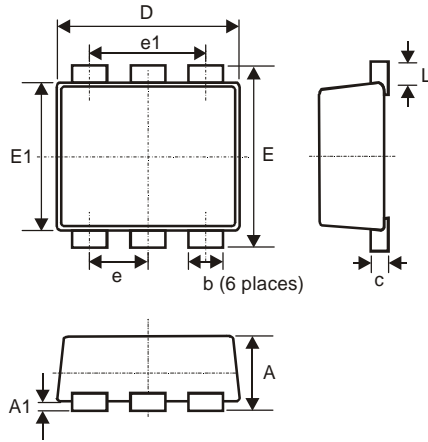


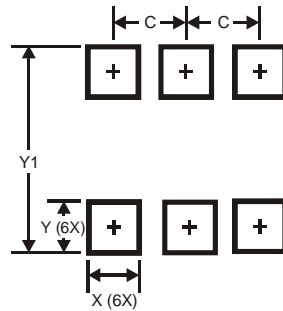
Fig. 17 Safe Operation Area (PNP)

**Package Outline Dimensions**



SOT-963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0	0.05	-
C	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
L	0.05	0.15	0.10
b	0.10	0.20	0.15
e	0.35 Typ		
e1	0.70 Typ		
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100



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